



For discussion purposes,

Top plot is graph 1 and bottom plot is graph 5

For clarity:

Graph 1 shows the CLK signal being used by the entire memory

Graph 2 shows PRECHbar signal used to precharge BL/BLB

Graph 3 shows:

- a local WL in green, which is created by the row decoder output ANDed with the block select output
- a local-local WL in pink, which is the local WL(green) passed through some logic to create control signals
- inDout0 in red, which is data bit 0 to be latched into the output register on the next falling CLK edge

Graph 4 shows BL in aqua and BLB in orange; Sense Amp Enable is in black

Graph 5 shows the output of the sense amp; OUT is red and OUTbar is blue

Graph 6 shows TXGControl in orange and TXGControlbar in green. These two signals control the transmission gate between the BL/BLB drivers and the actual BL/BLB.

Our measured delay was 0.7425 ns, which resulted in a CLK period of 1.425 ns.

- By buffering up the inDout signal (correct data from the specific block being sent through 2:1MUXes to the output register), we could've reduced our delay by ~150-200 ps alone.
- By just buffering up PRECHbar, we could've reduced our delay by ~100 ps.
- If we precharged after any given operation (when the CLK is low) we could've removed the precharge delay from our critical path completely and reduced our delay by ~200 ps. Then we would only worry about the local WL (green in graph 3) to dictate the beginning path of our read operation (as opposed to including precharging in the read operation).
- By examining the Sense Amp sizing more carefully, we could reduce the (voltage) amount BL/BLB and OUT/OUTbar drops, consequently reducing our delay by ~50 ps (or possibly more).

Combining these techniques together, we could have cut our delay in half, reducing our metric by 75%.